

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 11-121458  
(43)Date of publication of application : 30.04.1999

(51)Int.Cl. H01L 21/3205  
H01L 21/60  
// H01L 21/60

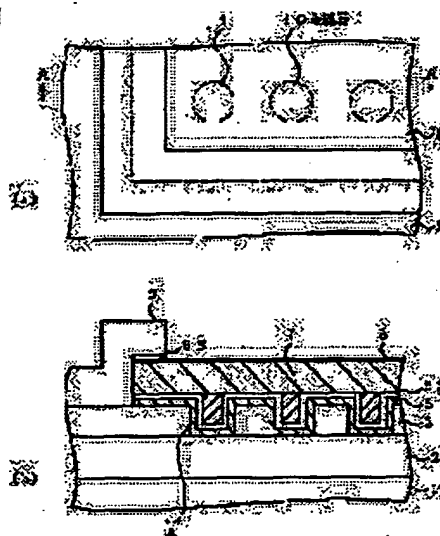
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## (54) SEMICONDUCTOR DEVICE

### (57)Abstract:

**PROBLEM TO BE SOLVED:** To provide an electrode pad where aluminum is not stripped by contacting a bottom of the electrode pad to a metal layer in a groove formed on an insulation film.

**SOLUTION:** A semiconductor device comprises an oxidation film 3 of about 1  $\mu\text{m}$  thickness which is formed on a semiconductor substrate 1, a groove 4 of 0.8  $\mu\text{m}$  diameter which is formed on the oxidation film 3, Ti film 5 of about 30 nm thickness formed on the film 3 containing the groove 4, TiN film 6A of about 100  $\mu\text{m}$  thickness, W film 7 imbedded in the groove 4, and electrode pad comprising Al alloy film 8 of about 600 nm thickness formed on the W film 7 and TiN film 6A. As a result, since the electrode pad is connected to a metal layer 10 formed in the groove 4 including the W film 7 and others, aluminum of the pad is not stripped even if wire bonding is achieved.



## LEGAL STATUS

[Date of request for examination] 21.10.1997

[Date of sending the examiner's decision of rejection] 14.08.2001

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

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